



Using the TPS40090EVM-002

User's Guide

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It is important to operate this EVM within the input voltage range of 0 Vdc to 100 Vdc.

Exceeding the specified input range may cause unexpected operation and/or irreversible damage to the EVM. If there are questions concerning the input range, please contact a TI field representative prior to connecting the input power.

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TPS40090 Multi-Phase Buck Converter and TPS2834 Drivers Steps-Down from 12-V to 1.5-V at 100 A

Systems Power

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1 Introduction

The TPS40090EVM-002 multi-phase dc-to-dc converter utilizes the TPS40090 multi-phase controller and TPS2834 adaptive driver to step down a 12-V input to 1.5-V at 420 kHz. The output current can exceed 100 A. The TPS40090 provides fixed-frequency, peak current-mode control with forced-phase current balancing. Phase currents are sensed by the voltage drop across the DC resistance (DCR) of inductors. Other features include a single voltage operation, true differential output voltage sense, user programmable current limit, capacitor-programmable soft-start and a power good indicator. Device operation is specified in the TPS40090 datasheet^[1].

TPS40090EVM-002 can be configured into 2-, 3- or 4-phase operation. For 2-phase operation, populate R65 and R66 to tie PWM2 and PWM4 up to internal 5-V and leave components in related phases unpopulated. For 3-phase operation, tie PWM4 to BP5 through R66 only. For 4-phase operation, leave both R65 and R66 unpopulated.

In this user’s guide, all the tests are conducted under 4 phase operation.

2 Features

Table 1. TPS40090EVM-002 Performance Summary

PARAMETER	TEST CONDITIONS	MIN	TYP	MAX	UNITS
Input voltage range		10.5	12.0	14.0	V
Output voltage set point		1.477	1.508	1.540	
Output current range	$V_{IN} = 12\text{ V}$	0	100	120	A
Line regulation(1)	I_{OUT} rising from 10 A to 100 A, $10.5\text{ V} \leq V_{IN} \leq 14\text{ V}$	±0.1%			
Load regulation	I_{OUT} rising from 10 A to 100 A	±0.3%			
Load transient response voltage change	I_{OUT} rising from 10 A to 100 A	-160			mV μ K
	I_{OUT} falling from 100 A to 10 A	200			
Load transient response recovery time	I_{OUT} rising from 10 A to 100 A	< 10			μ s
	I_{OUT} falling from 100 A to 10 A	< 15			
Loop bandwidth	$I_{OUT} = 100\text{ A}$, $I_{OUT} = 10\text{ A}$	89			kHz
Phase margin	$I_{OUT} = 100\text{ A}$	40			°
Input ripple voltage			80	200	mV μ K
Output ripple voltage			15	25	
Output rise time					ms
Operating frequency		370	418	454	kHz
Full load efficiency	$V_{IN} = 12\text{ V}$, $I_{OUT} = 100\text{ A}$	$V_{OUT} = 1.5\text{ V}$,		84.3%	
Current sharing tolerance	$V_{IN} = 12\text{ V}$, $I_{OUT} = 100\text{ A}$	$V_{OUT} = 1.5\text{ V}$,		±5% ±10%	

3 Schematic

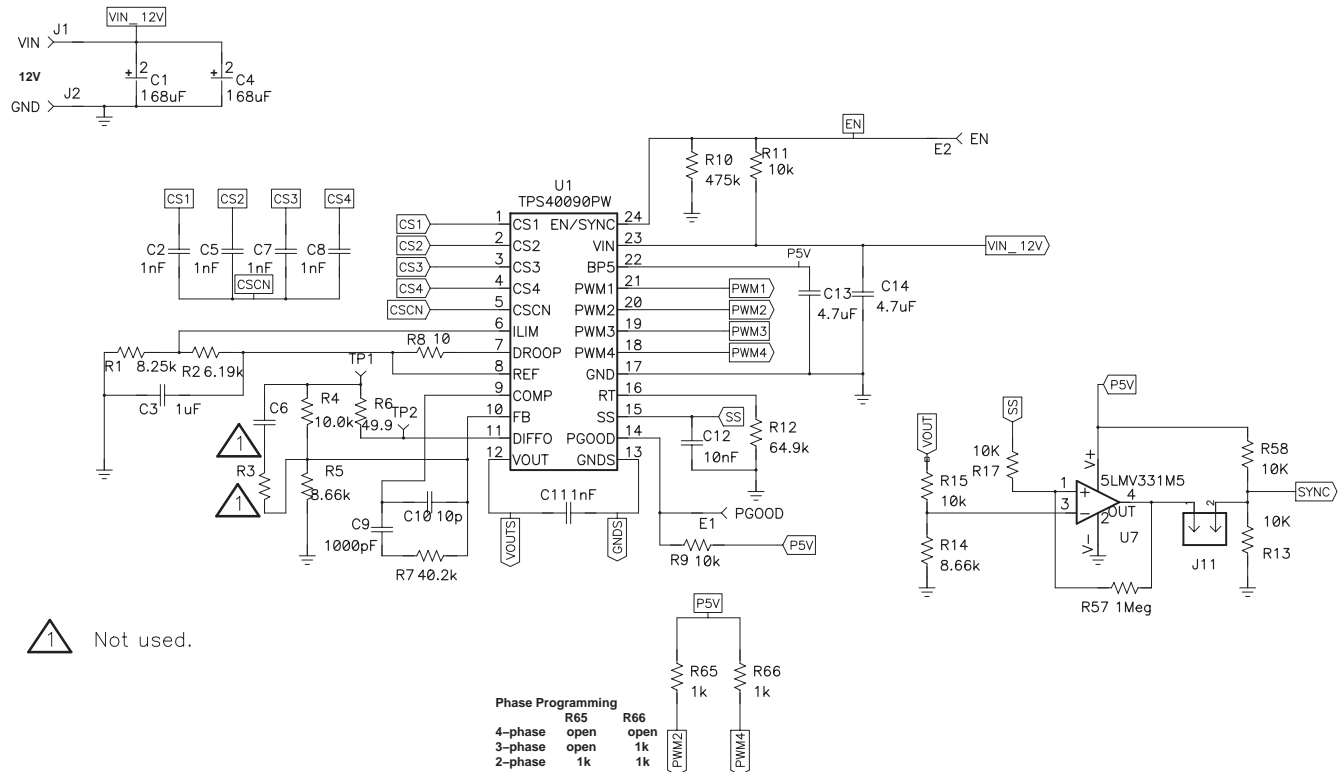
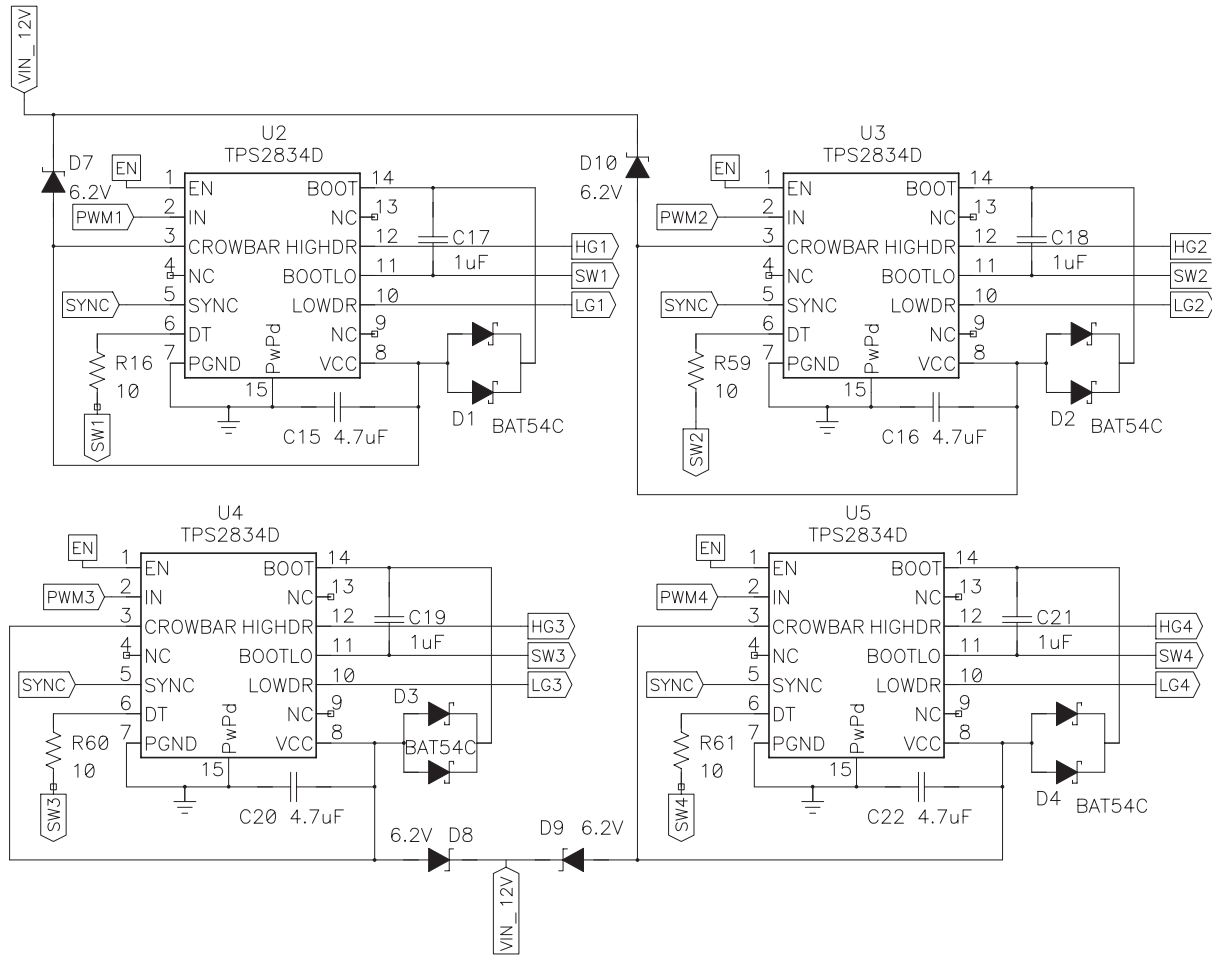


Figure 1. TPS40090EVM-002 Schematic Part 1 – TPS40090 Controller and Pre-Bias Circuit



1 Not used

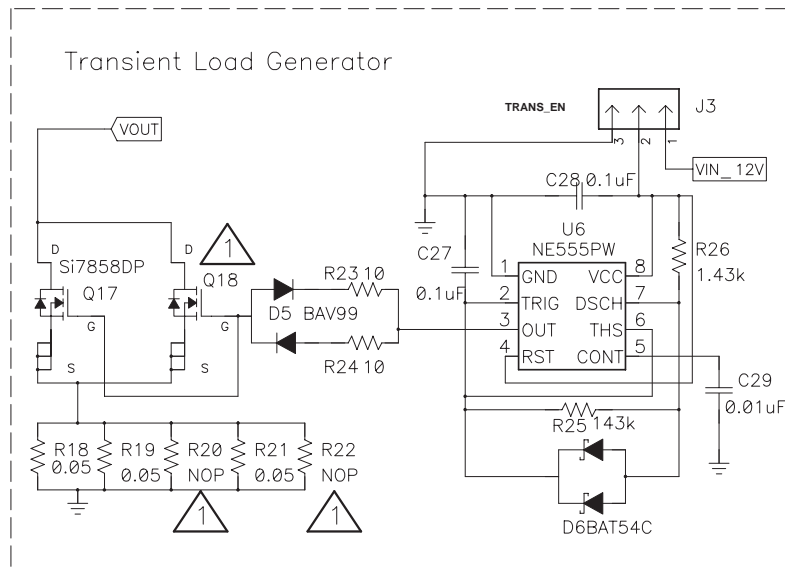


Figure 2. TPS40090EVM-002 Schematic Part 2 – Driver Circuit and Load Transient Generator

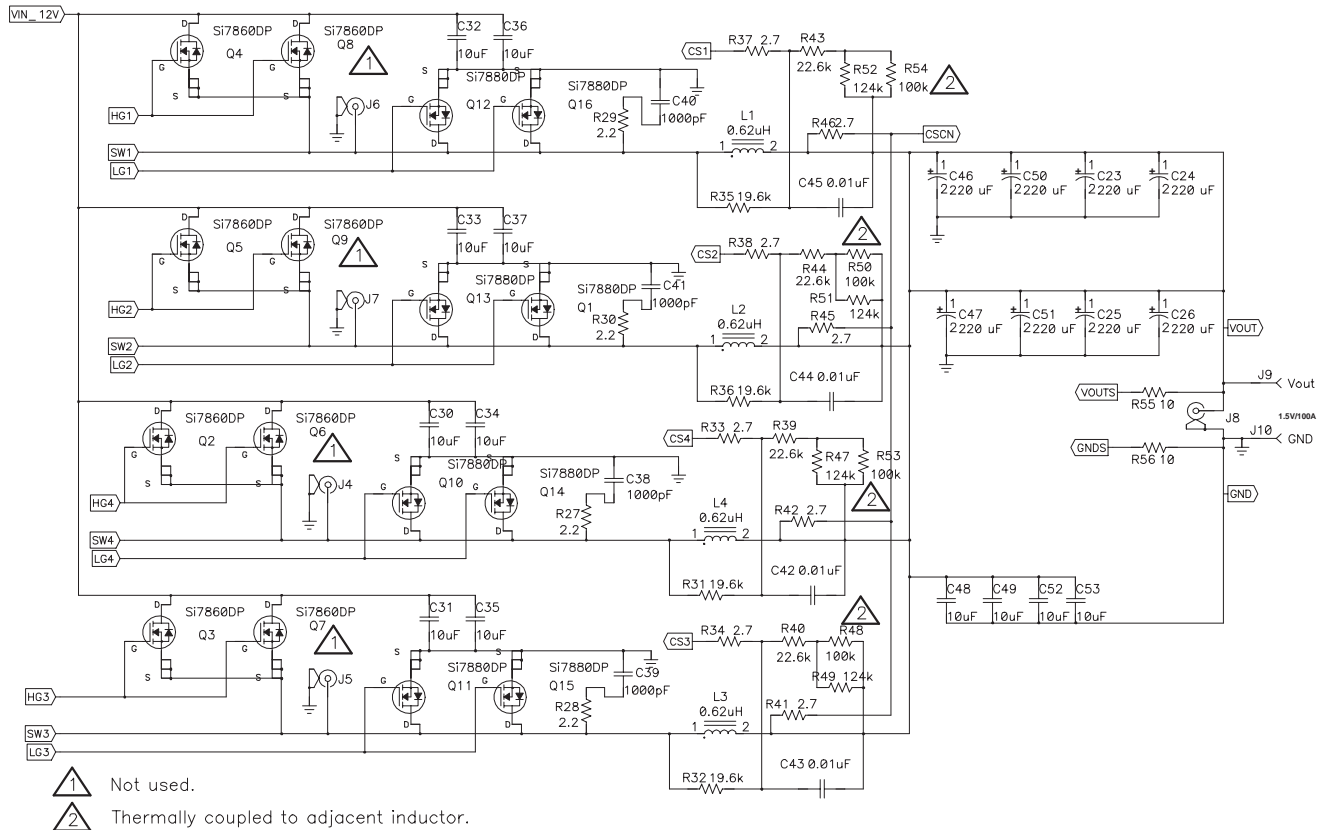


Figure 3. TPS40090EVM-002 Schematic Part 3 – Power Stage

4 Component Selection

4.1 Frequency of Operation

The clock oscillator frequency for the TPS40090 is programmed with a single resistor from RT (pin 16) to signal ground. Equation (1) from the datasheet allows selection of the R_T resistor in $k\Omega$ for a given switching frequency in kHz.

$$R_T = R_{12} = K_{PH} \times \left(39.2 \times 10^3 \times f_{PH}^{-1.024} - 7 \right) \text{ (k}\Omega\text{)} \quad (1)$$

where

- K_{PH} is the coefficient that depends on the number of active phases
- f_{PH} is the single phase frequency, in kHz
- for 2-phase and 3-phase configurations $K_{PH}=1.333$
- for 4-phase $K_{PH}=1.0$ is a single phase frequency, kHz.

The R_T resistor value is returned by the last expression in $k\Omega$. For 420 kHz, R_T is calculated as 65.8 $k\Omega$ and a resistor with a 64.9- $k\Omega$ standard value is used.

4.2 Inductance Value

The output inductor value for each phase can be calculated from the volt-second during off time, shown in equation (2).

$$L = \frac{V_{OUT}}{f \times I_{RIPPLE}} \times \left(1 - \frac{V_{OUT}}{V_{IN(max)}} \right) \quad (2)$$

where

- I_{RIPPLE} is usually chosen to be between 10% and 40% of maximum phase current $I_{PH(max)}$.

With $I_{RIPPLE} = 20\%$ of $I_{PH(max)}$, there is a ripple current of 5 A, and the inductance value is found to be 0.63 μH . Using SPM12550–R62M300 inductors from TDK, each had inductance of 0.6 μH and resistance of 1.75-m Ω .

In multi-phase high current buck converter design, due to the ripple cancellation factor from interleaving, the inductor value could be smaller than that in a single phase operation. But from conduction loss point of view, the inductor value tends to be big to reduce the ripple current, thus losses.

4.3 Input Capacitor Selection

The bulk input capacitor selection is based on the input voltage ripple requirements. Due to the interleaving of multi phase, the input RMS current is reduced. The input ripple current RMS value over load current is calculated in equation (3).

$$\Delta I_{IN(nom)}(N_{PH}, D) = \sqrt{\left[\left(D - \frac{k(N_{PH}, D)}{N_{PH}} \right) \times \left(\frac{k(N_{PH}, D) + 1}{N_{PH}} - D \right) \right] + \left(\frac{N_{PH}}{12 \times D^2} \right) \times \left[\frac{V_{OUT} \times (1 - D)}{L \times f \times (I_{OUT})} \right]^2} \times \sqrt{\left[\left(k(N_{PH}, D) + 1 \right)^2 \times \left(D - \frac{k(N_{PH}, D)}{N_{PH}} \right)^3 + k(N_{PH}, D)^2 \times \left(\frac{k(N_{PH}, D) + 1}{N_{PH}} - D \right)^3 \right]} \quad (3)$$

where

- $k(N_{PH}, D) = \text{floor}(N_{PH} \times D)$
- floor(x) is the function to return the greatest integer less than $N_{PH} \times D$
- N_{PH} is the number of active phases

Figure 4 shows the input ripple current RMS value over the load current versus duty cycle with different number of active phases.

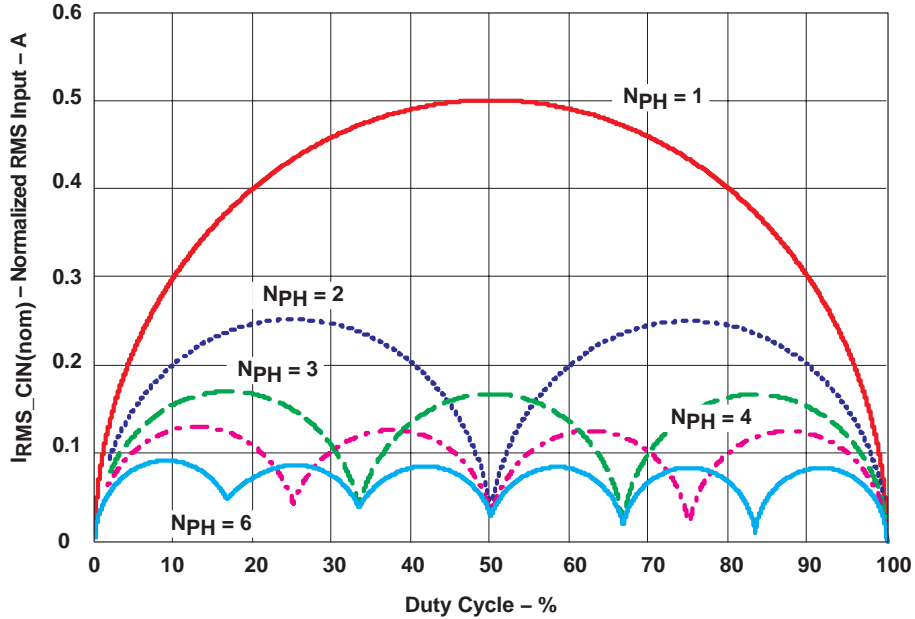


Figure 4. Input Ripple Current RMS Value Overload Current

The maximum input ripple RMS current can be estimated as shown in (4).

$$I \cong I_{OUT} \times \Delta I_{IN(nom)}(4, D_{min}) = 3.18 \text{ A} \quad (4)$$

It is also important to consider a minimum capacitance value which limits the voltage ripple to a specified value if all the current is supplied by the onboard capacitor. For a typical ripple voltage of 150 mV the maximum ESR is calculated in (5) as:

$$ESR = \frac{\Delta V}{\Delta I} = \frac{150 \text{ mV}}{3.18 \text{ A}} = 47 \text{ m}\Omega \quad (5)$$

Two 68- μ F, 20-V Oscon capacitors (20SVP68M) from Sanyo are placed on the input side of the board. The ESR is 40 m Ω for each capacitor.

4.4 Output Ripple Cancellation and Capacitor Selection

Due to the interleaving of channels, the total output ripple current is smaller than the ripple current from a single phase. The ripple cancellation factor is expressed in equation (6).

$$\Delta I_{OUT}(N_{PH}, D) = \frac{\left(\prod_{i=1}^{N_{PH}} |i - N_{PH} \times D| \right)}{\left[\prod_{i=1}^{N_{PH}-1} (|i - N_{PH} \times D| + 1) \right]} \quad (6)$$

$$k(N_{PH}, D) = \text{if} \left(N_{PH} \leq 1, \Delta I_{OUT}(D), \Delta I_{OUT}(N_{PH}, D) \right)$$

where

- D is the duty cycle for a single phase
- N_{PH} is the number of active phases
- $K(N_{PH})$ is the intermediate function for calculation

In this case, $N_{PH}=4$ and $D_{min}=0.107$ which yields $k=0.573$.

The actual output ripple is calculated in equation (7)

$$I_{RIPPLE} = \frac{V_{OUT}}{L \times f} \times K(N_{PH}, D) = \frac{1.5 \text{ V}}{0.6 \mu\text{ H} \times 420 \text{ kHz}} \times 0.573 = 3.41 \text{ A} \quad (7)$$

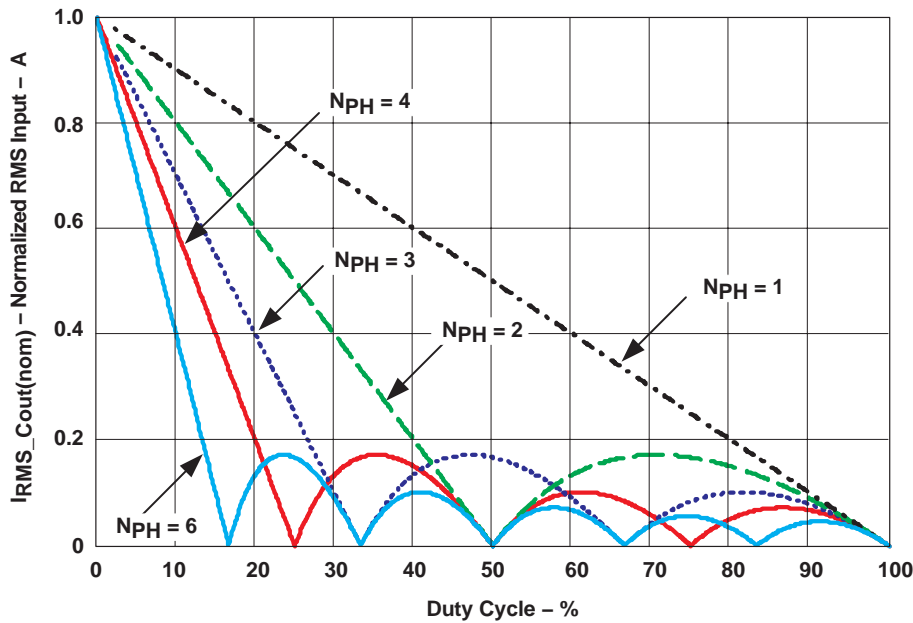


Figure 5. Output Ripple Current Cancellation

Selection of the output capacitor is based on many application variables, including function, cost, size, and availability. There are three ways to calculate the output capacitance.

1. The minimum allowable output capacitance is determined by the amount of inductor ripple current and the allowable output ripple, as given in equation (8).

$$C_{OUT(min)} = \frac{I_{RIPPLE}}{8 \times f \times V_{RIPPLE}} = \frac{3.41 \text{ A}}{8 \times 420 \text{ kHz} \times 10 \text{ mV}} = 101 \mu\text{F} \quad (8)$$

In this design, $C_{OUT(min)}$ is 101- μF with $V_{RIPPLE}=10 \text{ mV}$. However, this affects only the capacitive component of the ripple voltage, and the final value of capacitance is generally influenced by ESR and transient considerations.

2. ESR limitation. (To limit the ripple voltage to 10 mV, the capacitor ESR should be less than the value calculated in equation (9)).

$$R_C <= \frac{V_{RIPPLE}}{I_{RIPPLE}} = \frac{10 \text{ mV}}{3.41 \text{ A}} = 2.93 \text{ m}\Omega \quad (9)$$

3. Transient consideration. An additional consideration in the selection of the output inductor and capacitance value can be derived from examining the transient voltage overshoot which can be initiated with a load step from full load to no load. By equating the inductive energy with the capacitive energy the equation (10) can be derived.

$$C_{OUT} = \frac{L \times I^2}{V^2} = \frac{L_{EQ} \times \left((I_{OH})^2 - (I_{OL})^2 \right)}{\left(V_{OUT2} \right)^2 - \left(V_{OUT1} \right)^2} = \frac{\frac{0.6\mu\text{H}}{4} \times (100 \text{ A})^2}{\left((1.75 \text{ V})^2 - (1.5 \text{ V})^2 \right)} = 1846 \mu\text{F} \quad (10)$$

where

- I_{OH} is full load
- I_{OL} is no load
- V_{OUT2} is the the allowed transient voltage rise
- V_{OUT1} is the initial voltage

In this 100-A design the capacitance required for limiting the transient is significantly larger than the capacitance required to keep the ripple acceptably low. Eight 220- μF POSCAP capacitors are in parallel with four 22- μF ceramic capacitors. The ESR of each POSCAP is 15m Ω .

4.5 MOSFET Selection

There are different requirements for switching FET(s) and rectifier FET(s) in the high-ratio step down application. The duty cycle is around 12%. So the rectifier FET(s) is on for most of the cycle. The conduction loss is dominant. Low- $R_{DS(on)}$ FET(s) are preferred. Also due to the dV/dt turn on of the rectifier FET(s) and cross conduction, choose a rectifier FET with $Q_{gs} > Q_{gd}$. When the switch node is falling, the Q_{gd} can pull the gate of the lower FET below GND, which upsets the driver. Two Si7880DP from Siliconix are in parallel for the rectifier FET. The $R_{DS(on)}$ of this FET is 3 m Ω and $Q_{gs}=18\text{nC}$, and $Q_{gd}=10.5\text{nC}$.

The switching FET switches at high voltage and high current, the switching loss is dominant. One single Si7860DP is selected for its low total gate charge.

Both types of FET(s) are offered in the Powerpak SO-8 package.

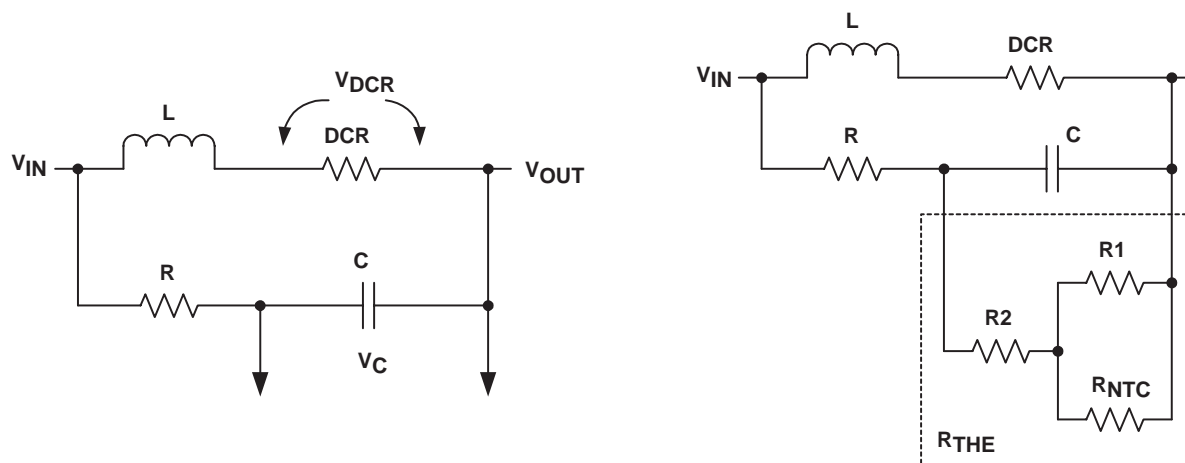
The PCB is layed out for two FETs in parallel, for both switching FET(s) and rectifier FET(s), to give the feasibility to modify the board for different applications.

4.6 Current Sensing

TPS40090 supports both resistor current sensing and DCR current sensing approach. DCRs of the output inductors are used in this design as the current sensing components. The DCR current sensing circuit is shown in Figure 5. The idea is to parallel a R-C network to the inductor. If the two time constants are same ($L/DCR=R \times C$), then $V_C=V_{DCR}$. Extra circuit, shown in (b), is used to compensate the positive temperature coefficient of copper specific resistance, which is 0.385%/°C. See detail explanation in the datasheet.

With the chosen inductor described in *Inductance Value*, (section 4.2, of this document) the following values are used.

- R=19.6 kΩ
- C=10 nF
- R_{NTC}=100 kΩ
- R1=124 kΩ
- R2=22.6 kΩ



UDG-03136

Figure 6. DCR Current Sensing Circuit with Copper Temperature Compensation

4.7 Overcurrent Limit Protection

The overcurrent function monitors the voltage level separately on each current sense input and compares it to the voltage on ILIM pin set by the divider from the controller’s reference.

If the threshold of $V_{ILIM}/2.7$ is exceeded, the PWM cycle on the respected phase is terminated. Voltage level on the ILIM pin is determined by (11).

$$V_{ILIM} = 2.7 \times I_{PH(max)} \times R_{CS}; \quad I_{PH(max)} = I_{OUT} + \frac{(V_{IN} - V_{OUT}) \times V_{OUT}}{2 \times L_{OUT} \times f_{SW} \times V_{IN}} \tag{11}$$

where

- $I_{PH(max)}$ is the maximum allowable value of the phase current
- R_{CS} is the value of the current sense resistor

4.8 Compensation Components

The TPS40090 uses peak current mode control. Type II network is used here, which is implemented to provide one zero and two poles. The first pole is placed at the origin to improve DC regulation.

The ESR zero of the power stage is:

$$f_{\text{ESRZ}} = \frac{1}{2\pi \times R_C \times C_{\text{OUT}}} = 354 \text{ kHz} \quad (12)$$

The zero is placed near 3.96 kHz to produce a reasonable time constant.

$$f_Z = \frac{1}{2\pi \times R7 \times C9} \quad (13)$$

The second pole is placed at ESR zero (354 kHz).

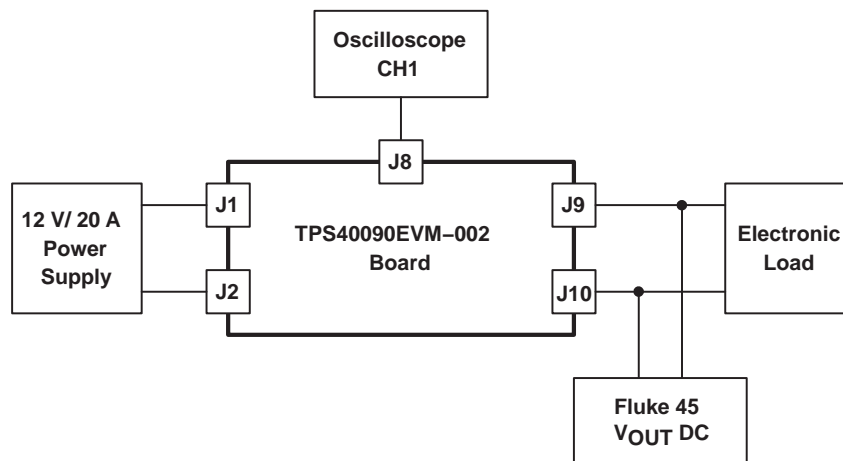
$$f_{\text{P1}} = \frac{1}{2\pi \times R7 \times \left(\frac{(C9 \times C10)}{(C9 + C10)} \right)} \quad (14)$$

The resulting values selected for this design are:

- R7 = 40.2 kΩ
- C9 = 1000 pF
- C10 = 10 pF

5 Test Setup

The HPA072 has the following input/output connections: 12-V input J1 (VIN) and J2 (GND), 1.5-V output J9 (VOUT) and J10 (GND). A diagram showing the connection points is shown in Figure 5. A power supply capable of supplying 18 A should be connected to VIN and GND through a pair of 10 AWG wires. The 1.5-V load should be connected respectively to J9 and J10 through pairs of 0 AWG wires. Wire lengths should be minimized to reduce losses in the wires. A 5-inch fan with 200-cfm air flow is recommended to operate this board at full load.



UDG-04063

Figure 7. Connections for the Test

6 Test Results and Performance Data

6.1 Efficiency and Power Loss

Figure 8 shows the efficiency as the load varies from 10 A to over 100 A. The efficiency at full load is about 84.3%.

Figure 7 shows the total loss versus the load current, which is approximately 28.3W at 100 A.

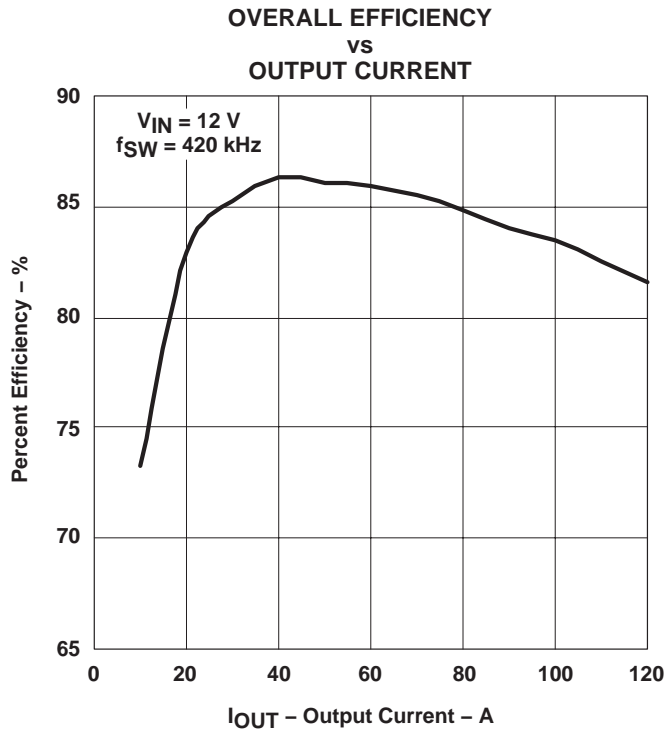


Figure 8.

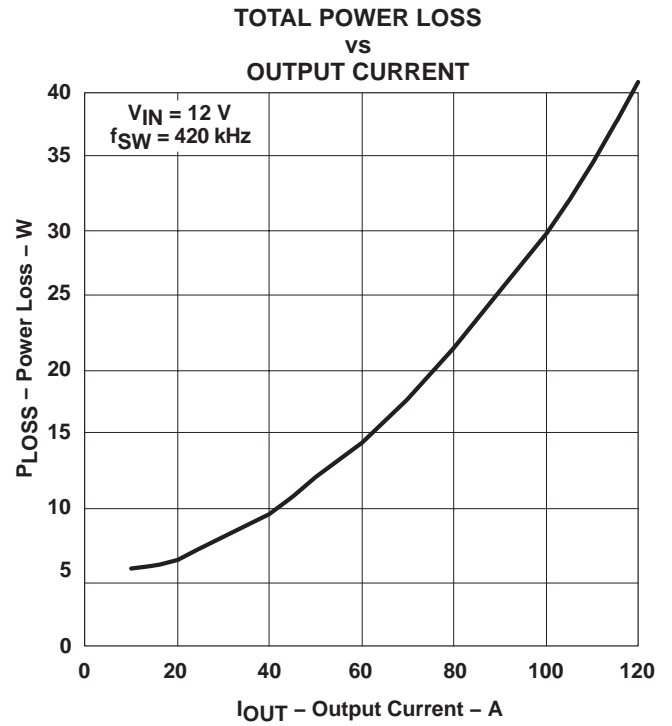


Figure 9.

6.2 Closed-Loop Performance

The TPS40090 uses peak current-mode control. Figure 10 shows the bode plots at 100 A of load current, where no droop function is implemented. The crossover frequency is at 89 kHz with phase margin of 40°.

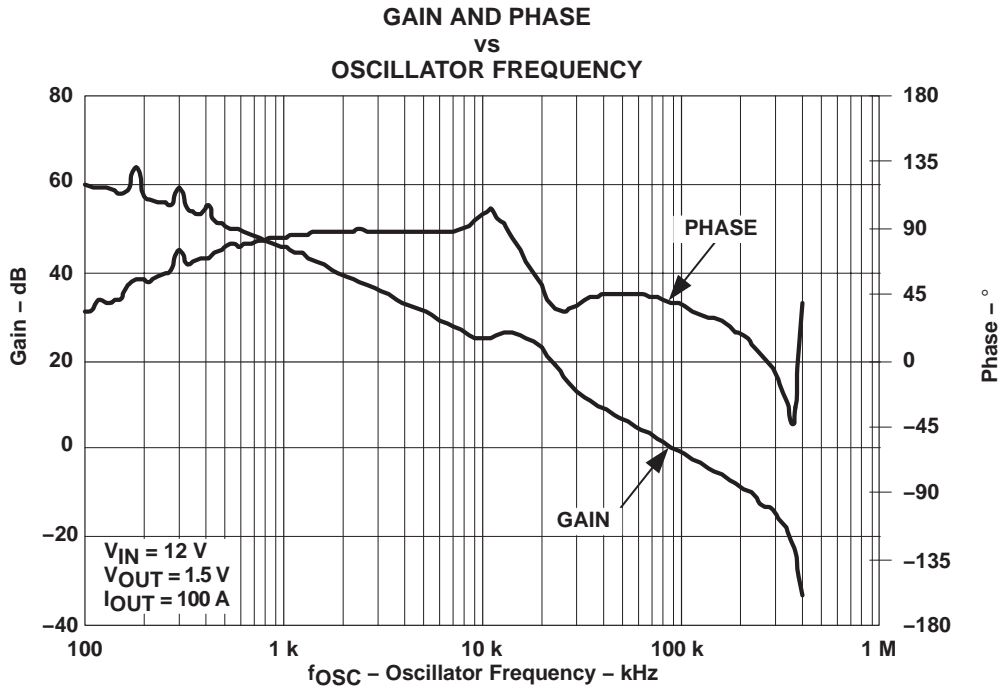


Figure 10. Bode Plot

6.3 Output Ripple and Noise

Figure 11 shows typical output noise where $V_{IN}=12\text{ V}$, and $I_{OUT}=100\text{A}$. The output ripple is less than 10 mV.

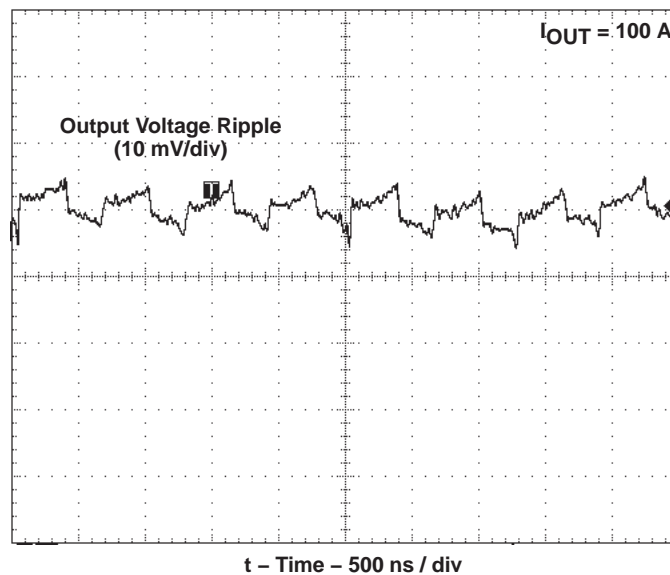


Figure 11. Output Noise

6.4 Transient Response

The on-board load transient circuit enables to check the step load transient response on the same board. Simply by putting a jumper to connect Pin1 and 2 of J3, a 90-A step load is created by three 50-m Ω resistors placed on the board. The slew rates of the transient are 200 A/ μ s for the load step-down and 160 A/ μ s for the load step-up.

The transient response is shown in Figure 6 as the load is stepped from 10 to 100 A. The output deviation is approximately 200 mV and the settling time is within 15 μ s.

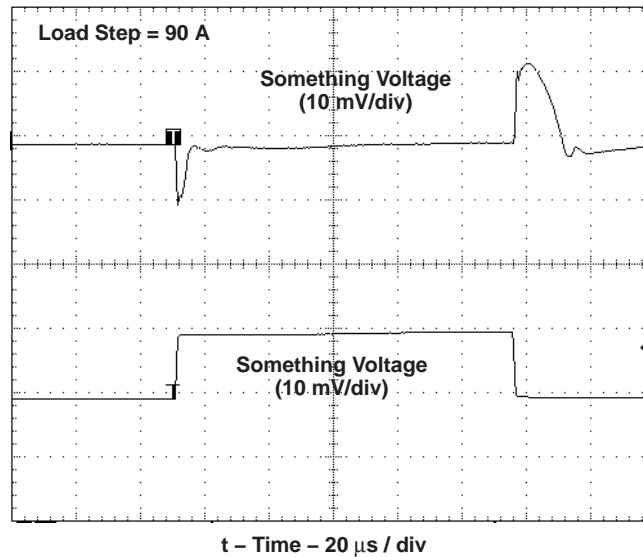
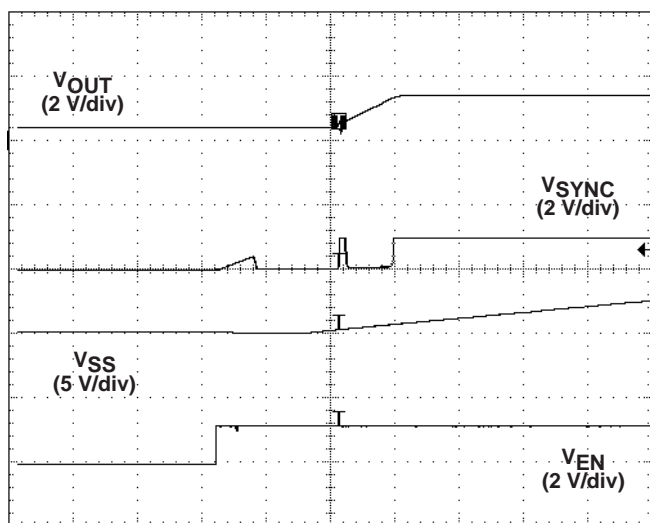


Figure 12. Transient Response

6.5 Start up with Pre-Biased Output

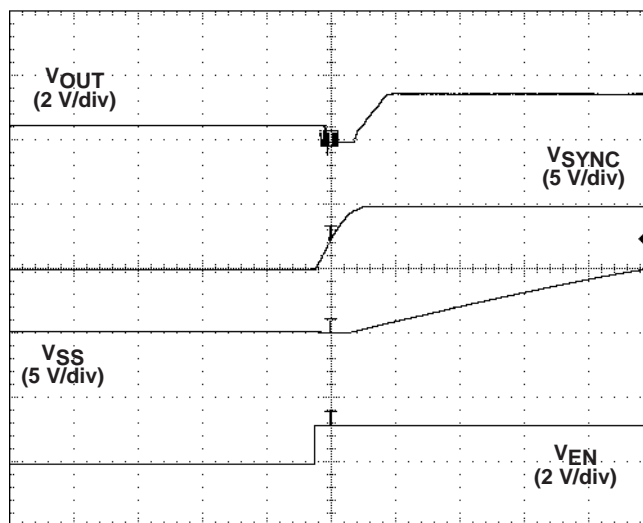
In synchronous buck converter, the bottom FET discharges the pre-biased output during start-up. To avoid this, a comparator U9 and surround components are used to pull the SYNC pin of the drivers low, which keeps the bottom FET off during startup. So the output can rise smoothly. After the SS pin comes up, SYNC is pulled up high and enable the bottom FET's driving signal. The converter goes back to normal synchronization mode. This function can be enabled by shorting J11 on the board.

Figure 8 shows the start-up waveform with pre-biased output with J11 short and open respectively. In Figure 12, there are two glitches of SYNC waveform. The first one is cause by P5V from TPS40090. When TPS40090 is enabled, P5V comes up first. SYNC is connected to P5V through a divider. The second one happens when the driver is ready and turns on the bottom FET when PWM signal is low. So the pre-biased output is pulled low which causes the SYNC signal high to turn off the bottom FET. Then output voltage goes back and rises up smoothly.



t – Time – 1 ms / div

Figure 13. J11 Short Circuit



t – Time – 2.5 ms / div

Figure 14. J11 Open Circuit

7 Layout Considerations

The PCB layout plays a critical role in the performance in a high frequency switching power supply design. Following the suggestions listed below will help to improve the performance and expedite the design.

- To take full advantage of the ripple cancellation factor from interleaving, place the input capacitors before the junction where the input voltage is distributed to each phase. Place the output capacitors after the junction where all the inductors are connected;
- Place the external drivers right next to the FETs and use at least 25 mil trace for gate drive signal to improve noise immunity
- Place some ceramic capacitors in the input of each channel to filter the current spikes
- Place the NTC resistor right next to its related inductor for better thermal coupling
- 2 oz. or thicker copper is recommended to reduce the trace impedance
- Place enough vias along pads of the power components to increase thermal conduction
- Keep the current sensing traces as short as possible to avoid excessive noise pick up
- Place the output inductors as symmetric as possible in relation to the output connectors to obtain similar voltage drop from the trace impedance

8 EVM Assembly Drawing and PCB Layout

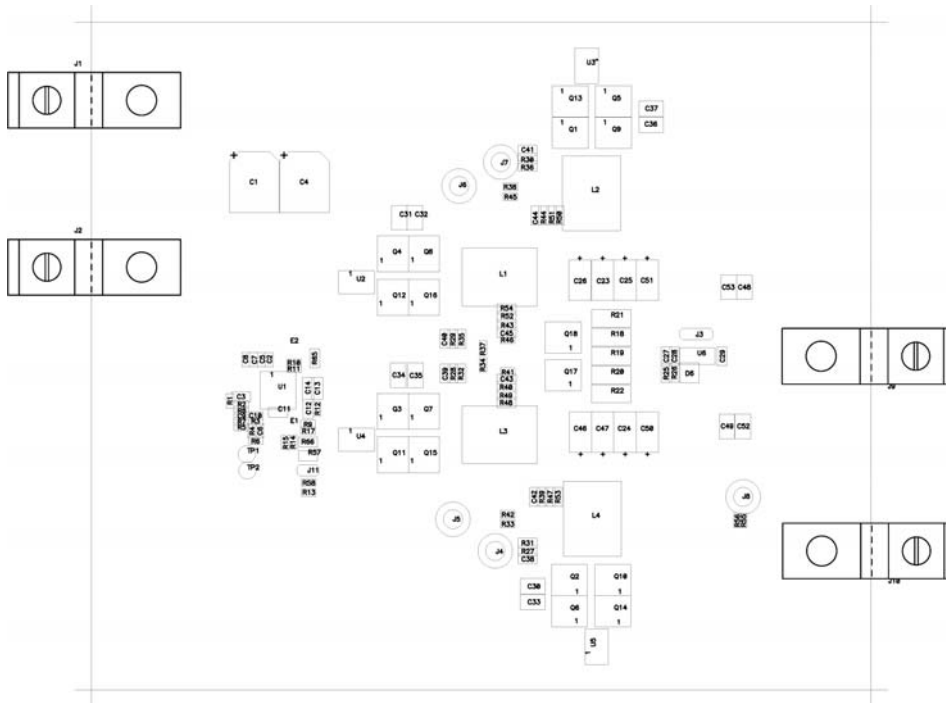


Figure 15. Top Side Component Assembly

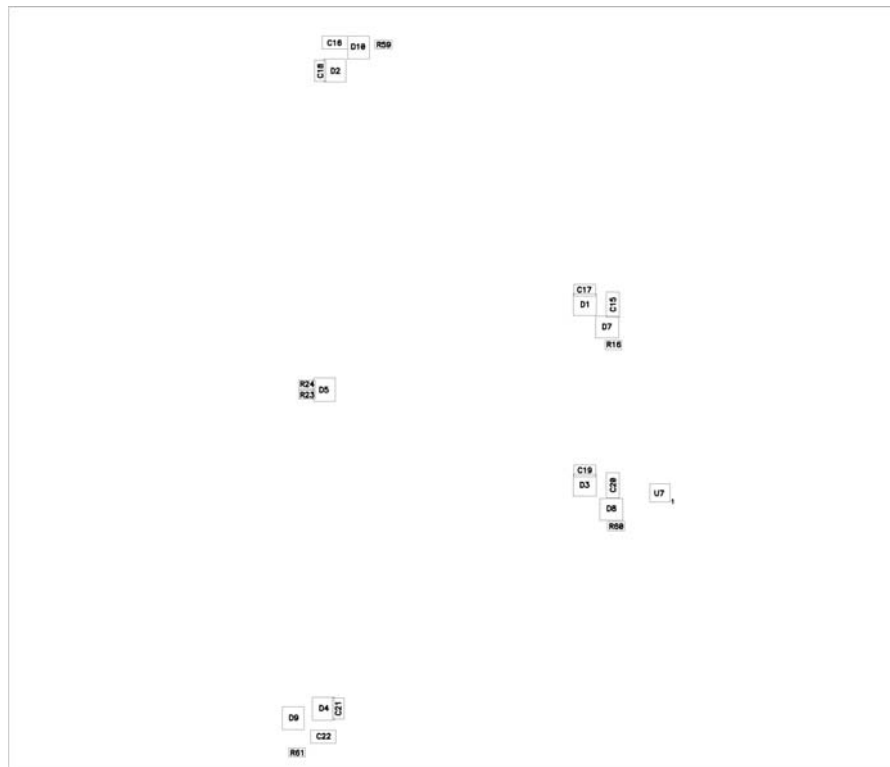


Figure 16. Bottom Assembly

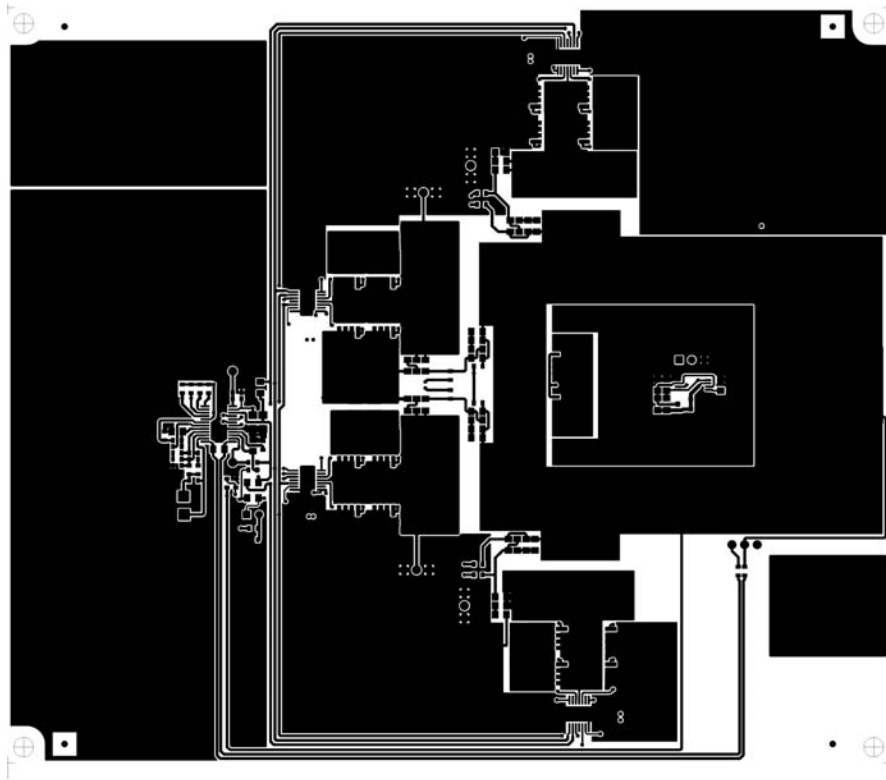


Figure 17. Top Side Copper

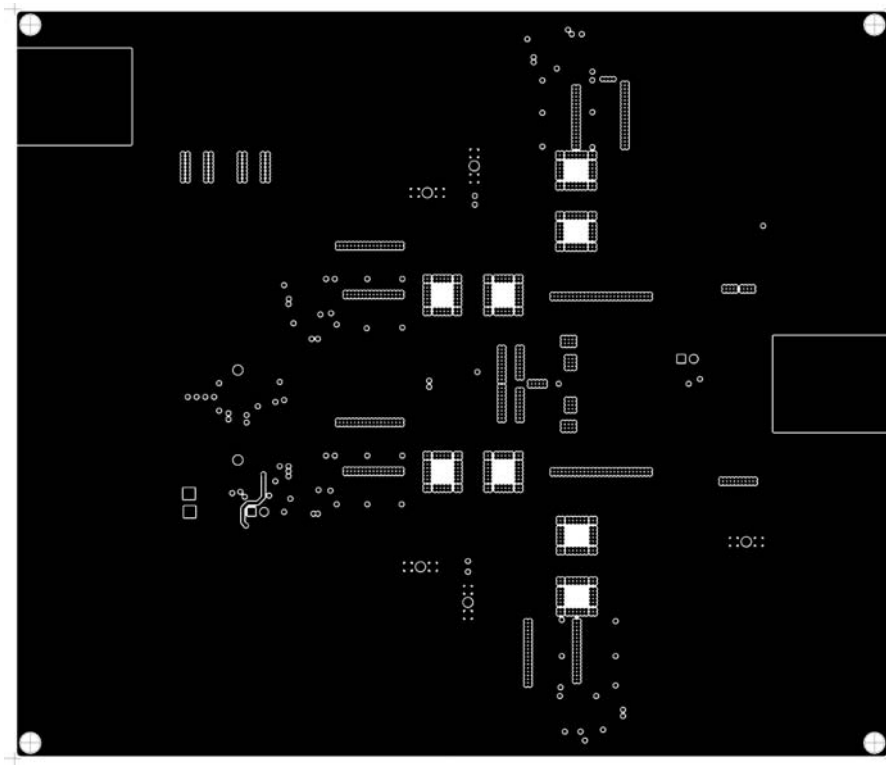


Figure 18. Internal 1 (Ground Plane)

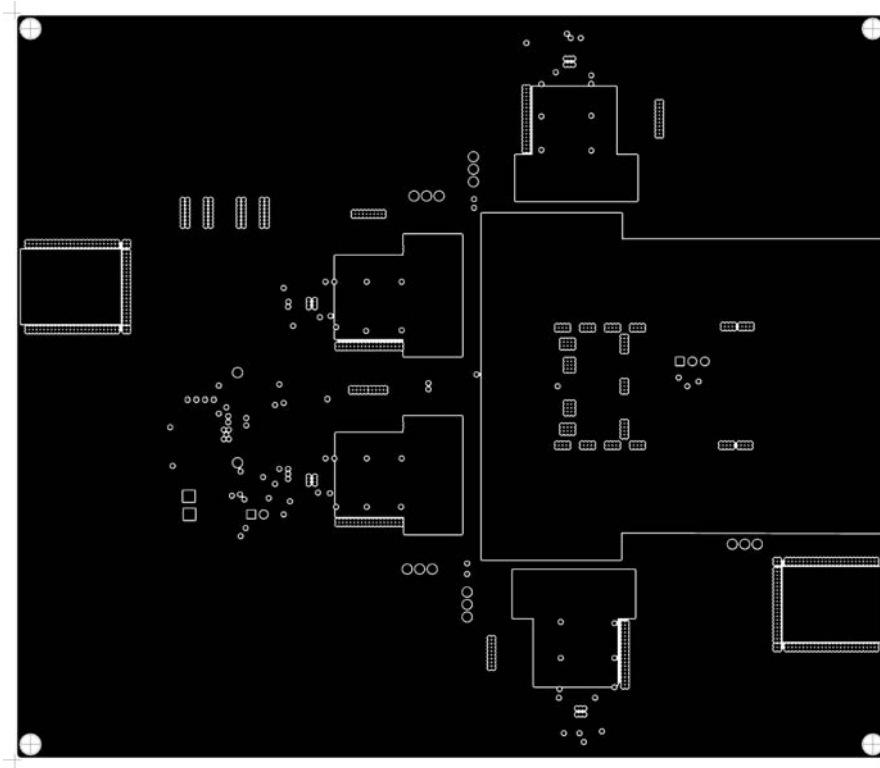


Figure 19. Internal 2 (Power Plane)

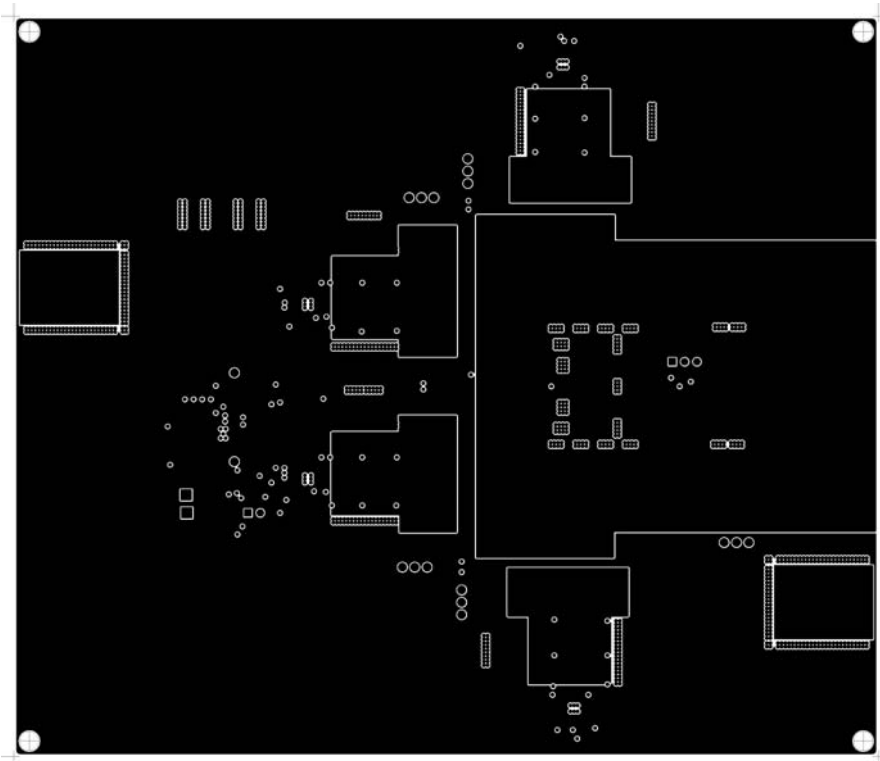


Figure 20. Internal 3

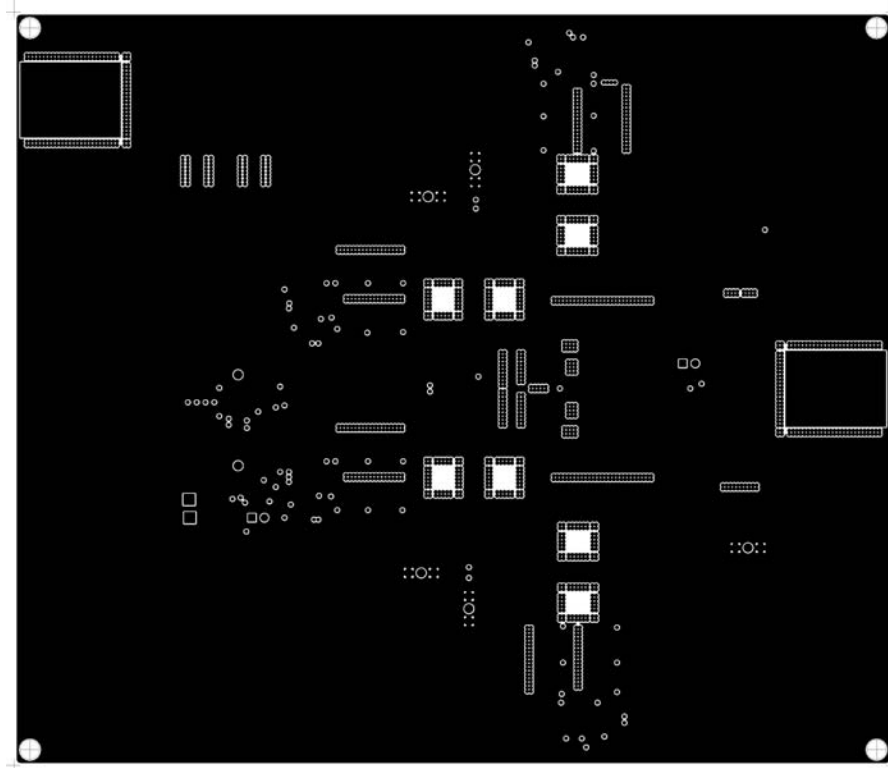


Figure 21. Internal 4

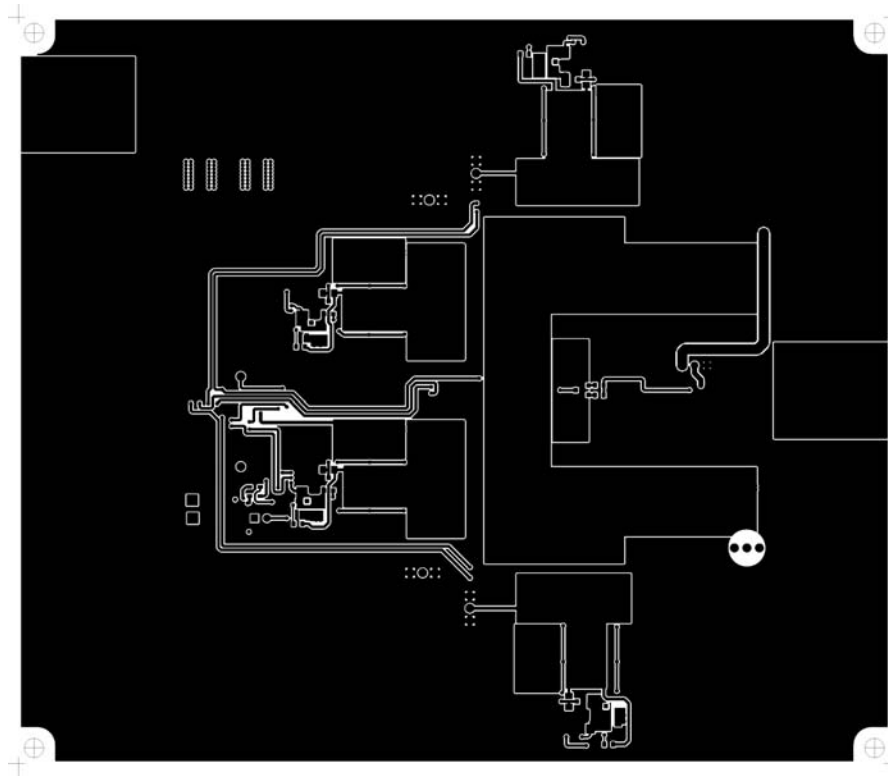


Figure 22. Bottom Layer Copper

9 List of Materials

The following table lists the TPS40090EVM–002 components corresponding to the schematic shown in Figure 1.

Table 2. List of Materials

Reference Designator	QTY	Description	Size	Manufacturer	Part Number
C1, C4	2	Capacitor, OS–CON, 68 μ F, 20 V, 40 m Ω , 20%	10.3mm (F8)	Sanyo	20SVP68M
C2, C5, C7, C8, C9, C11	6	Capacitor, ceramic, 1000–pF, 25 V, X7R, \pm 5%	603	muRata	GRM39SL102J25
C3, C17, C18, C19, C21	5	Capacitor, dielectric, 1.0 μ F, 16 V, X7R, \pm 10%	805	muRata	GRM40B105K16
C6	0		603	Std	Std
C10	1	Capacitor, ceramic, 10 pF, 50 V, COG, +2.5%	603	muRata	GRQ706COG100C50
C12	1	Capacitor, ceramic, 0.01 μ F, 50 V, X7R, \pm 5%	805	muRata	GRM40UJ103J50
C13, C14, C15, C16, C20, C22	6	Capacitor, dielectric, 4.7 μ F, 16 V, X5R, \pm 10%	1206	muRata	GRM42–65X5R475K16
C30, C31, C32, C33, C34, C35, C36, C37	8	Capacitor, dielectric, 10 μ F, 25 V, X5R	1210	TDK	C3225X5R1E106M
C38, C39, C40, C41	4	Capacitor, ceramic, 1000–pF, 50 V, X7R, \pm 5%	805	muRata	GRM40TH102J50
C42, C43, C44, C45	4	Capacitor, ceramic, 0.01 μ F, 50 V, COG	805	TDK	C2012COG1H103JT
C23, C24, C25, C26, C46, C47, C50, C51	8	Capacitor, POSCAP, 220 μ F, 2.5 V, 15 m Ω , 20%	7343 (D)	Sanyo	2R5TPE220M
C48, C49, C52, C53	4	Capacitor, Ceramic, 10 μ F, 6.3 V, X5R	1206	TDK	C3216X5R0J106M
D1, D2, D3, D4, D6	5	Diode, dual schottky, 200 mA, 30 V	SOT-23	Vishay–Liteon	BAT54C
D7, D8, D9, D10	4	Diode, zener, 6.2 V, 350 mW	SOT–23	Diodes, Inc.	BZX84C6V2
J1, J2, J9, J10	1	Lug, Solderless, #2 – #8 AWG, 1/4	Copper	524600	ILSCO
J4, J5, J6, J7, J8	5	Connector, shielded, test jack, vertical	0.0125 DIA	Johnson Components	129–0701–202
L1, L2, L3, L4	4	Inductor, SMT, 0.62 μ H, 30 A, 1.75 m Ω	0.524 x 0.492	TDK	SPM12550–R62M300
Q2, Q3, Q4, Q5	4	MOSFET, N-channel, 30 V, 18 A, 8.0 m Ω	PWRPAK S0–8	Vishay–Siliconix	Si7860DP
Q6, Q7, Q8, Q9	0	MOSFET, N-channel, 30 V, 18 A, 8.0 m Ω	PWRPAK S0–8	Vishay–Siliconix	Si7860DP
Q1, Q10, Q11, Q12, Q13, Q14, Q15, Q16	8	MOSFET, N-channel, 30 V, 29 A, 3 m Ω	PWRPAK S0–8	Vishay–Siliconix	Si7880DP
R1	1	Resistor, chip, 8.25 k Ω , 1/16–W, 1%	603	Std	Std
R2	1	Resistor, chip, 6.19 k Ω , 1/16–W, 1%	603	Std	Std
R3	0		603	Std	Std
R4, R9, R11	3	Resistor, chip, 10 k Ω , 1/16–W, 1%	603	Std	Std
R5	1	Resistor, chip, 8.66 k Ω , 1/16–W, 1%	603	Std	Std
R6	1	Resistor, chip, 49.9 Ω , 1/16–W, 1%	603	Std	Std
R7	1	Resistor, chip, 40.2 k Ω , 1/16–W, 1%	603	Std	Std
R8, R16, R55, R56, R59, R60, R61	7	Resistor, chip, 10–Ohms, 1/16–W, 1%	603	Std	Std
R10	1	Resistor, chip, 475 k Ω , 1/16–W, 5%	603	Std	Std
R12	1	Resistor, chip, 64.9 k Ω , 1/16–W, 1%	603	Std	Std

Reference Designator	QTY	Description	Size	Manufacturer	Part Number
R27, R28, R29, R30	4	Resistor, chip, 2.2 Ω , 1/10–W, 1%	805	Std	Std
R31, R32, R35, R36	4	Resistor, chip, 19.6 k Ω , 1/10–W, 1%	805	Std	Std
R33, R34, R37, R38, R41, R42, R45, R46	8	Resistor, chip, 2.7 Ω , 1/16–W, 1%	603	Std	Std
R39, R40, R43, R44	4	Resistor, chip, 22.6 k Ω , 1/10–W, 1%	805	Std	Std
R47, R49, R51, R52	4	Resistor, chip, 124 k Ω , 1/10–W, 1%	805	Std	Std
R48, R50, R53, R54	4	NTC Resistor, chip, 100 k Ω , 1/10–W, 1%	805	Vishay	NTHS0603N01N1003 J
R65, R66	2	Resistor, chip, 1.0 k Ω , 1/10–W, 1%	805	Std	Std
TP1	1	Test point, 0.062 Hole, Red	0.25	Keystone	5011
TP2	1	Test point, 0.062 Hole, Black	0.25	Keystone	5010
U1	1	IC, high-frequency, multiphase controller	108,800	TI	TPS40090PW
U2, U3, U4, U5	4	IC, MOSFET driver, fast synchronous buck with DTC	PWP14	TI	TPS2834PWP
U6	1	IC, Precision timer	TSSOP 8	TI	NE555PW
E1, E2	2	Test point, black, 1 mm	0.038	Farnell	240–333
LOAD TRANSIENT CIRCUIT					
Q17	1	MOSFET, N-channel, 12 V, 29 A, 3.0 m Ω ,	PWRPAK S0–8		Si7858DP
Q18	0	MOSFET, N-channel, 12 V, 29 A, 3.0 m Ω ,	PWRPAK S0–8		Si7858DP
R18, R19, R21	3	Resistor, chip, 0.050 Ω , 1–W, 0.5%	2512	Vishay	WSL–2512–R050 0.5% R86
R20, R22	0	Resistor, chip, 0.050 Ω , 1–W, 0.5%	2512	Vishay	WSL–2512–R050 0.5% R86
R23, R24	2	Resistor, chip, 10 Ω , 1/16–W, 1%	603	Std	Std
R25	1	Resistor, chip, 143 k Ω , 1/10–W, 1%	805	Std	Std
R26	1	Resistor, chip, 1.43 k Ω , 1/10–W, 1%	805	Std	Std
C27, C28	2	Capacitor, ceramic, 0.1 μ F, 25 V, X7R, \pm 10%	805	TDK	C2012X7R1E104K
C29	1	Capacitor, ceramic, 0.01 μ F, 50 V, X7R, \pm 5%	805	muRata	GRM40UJ103J50
D5	1	Diode, dual ultra fast, series, 200 mA, 70 V	SOT23	Fairchild	BAV99
D6	1	Diode, dual schottky, 200 mA, 30 V	SOT23	Vishay–Liteon	BAT54C
J3	1	Header, 3-pin, 100 mil spacing, (36-pin strip)	0.100 x 3	Sullins	PTC36SAAN
PRE-BIAS CIRCUIT					
U7	1	IC, Single GP comparator, low voltage	SOT23–5	National	LMV331M5
J11	1	Header, 2-pin, 100 mil spacing, (36-pin strip)	0.100 x 2	Sullins	PTC36SAAN
R13, R15, R17, R58	4	Resistor, chip, 10 k Ω , 1/16–W, 1%	603	Std	Std
R57	1	Resistor, chip, 1 M Ω , 1/10–W, 1%	805	Std	Std
R14	1	Resistor, chip, 8.66 k Ω , 1/16–W, 1%	603	Std	Std

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